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(NE)
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Entry
3/5/03

204612US-2

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :

YUUICHI HIRANO ET AL. : EXAMINER: TRAN, T.

SERIAL NO: 09/802,886 :

FILED: MARCH 12, 2001 : GROUP ART UNIT: 2811

FOR: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

RESPONSE

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action of November 8, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend independent Claim 1 to read as follows:[1]

SUB C1 7

1. (Twice Amended) A semiconductor device comprising:

an SOI substrate having a structure in which a semiconductor substrate, an insulating layer and a semiconductor layer are layered in this order;

B1

a partial-isolation insulating film formed in a main surface of said semiconductor layer;

[1]A marked-up copy of the amendments is attached hereto.